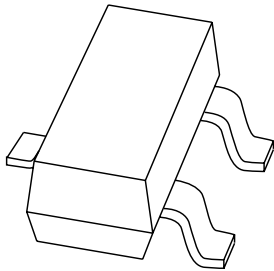


DATA SHEET



PMBT6428; PMBT6429 NPN general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 27

2004 Jan 22

NPN general purpose transistors

PMBT6428; PMBT6429

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 50 V).

APPLICATIONS

- General purpose switching and amplification
- Telephony and professional communication equipment.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

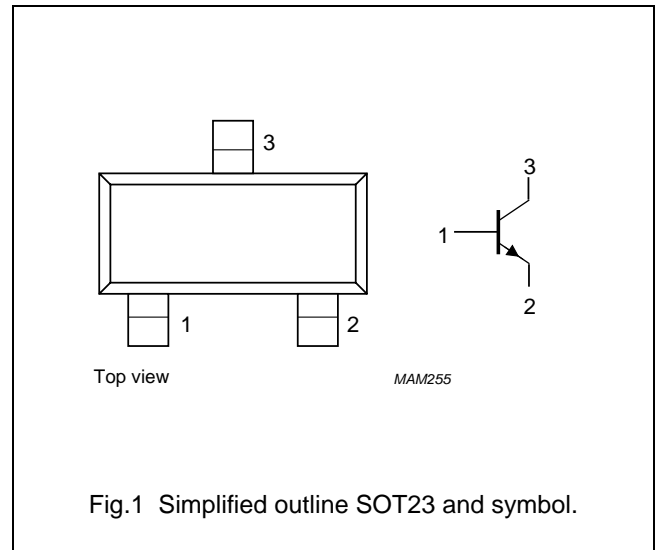
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT6428	*1K
PMBT6429	*1L

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT6428	–	plastic surface mounted package; 3 leads	SOT23
PMBT6429			

NPN general purpose transistors

PMBT6428; PMBT6429

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	PMBT6428		–	60	V
	PMBT6429		–	55	V
V _{CEO}	collector-emitter voltage	open base			
	PMBT6428		–	50	V
	PMBT6429		–	45	V
V _{EBO}	emitter-base voltage	open collector	–	6	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

PMBT6428; PMBT6429

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	10	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain PMBT6428	$I_C = 0.1\text{ mA}; V_{CE} = 5\text{ V}$	250	650	
			500	1250	
	DC current gain PMBT6428	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	250	–	
			500	–	
	DC current gain PMBT6428	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	250	–	
			500	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	200	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	600	mV
V_{BE}	base-emitter voltage	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	560	660	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	3	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	700	MHz

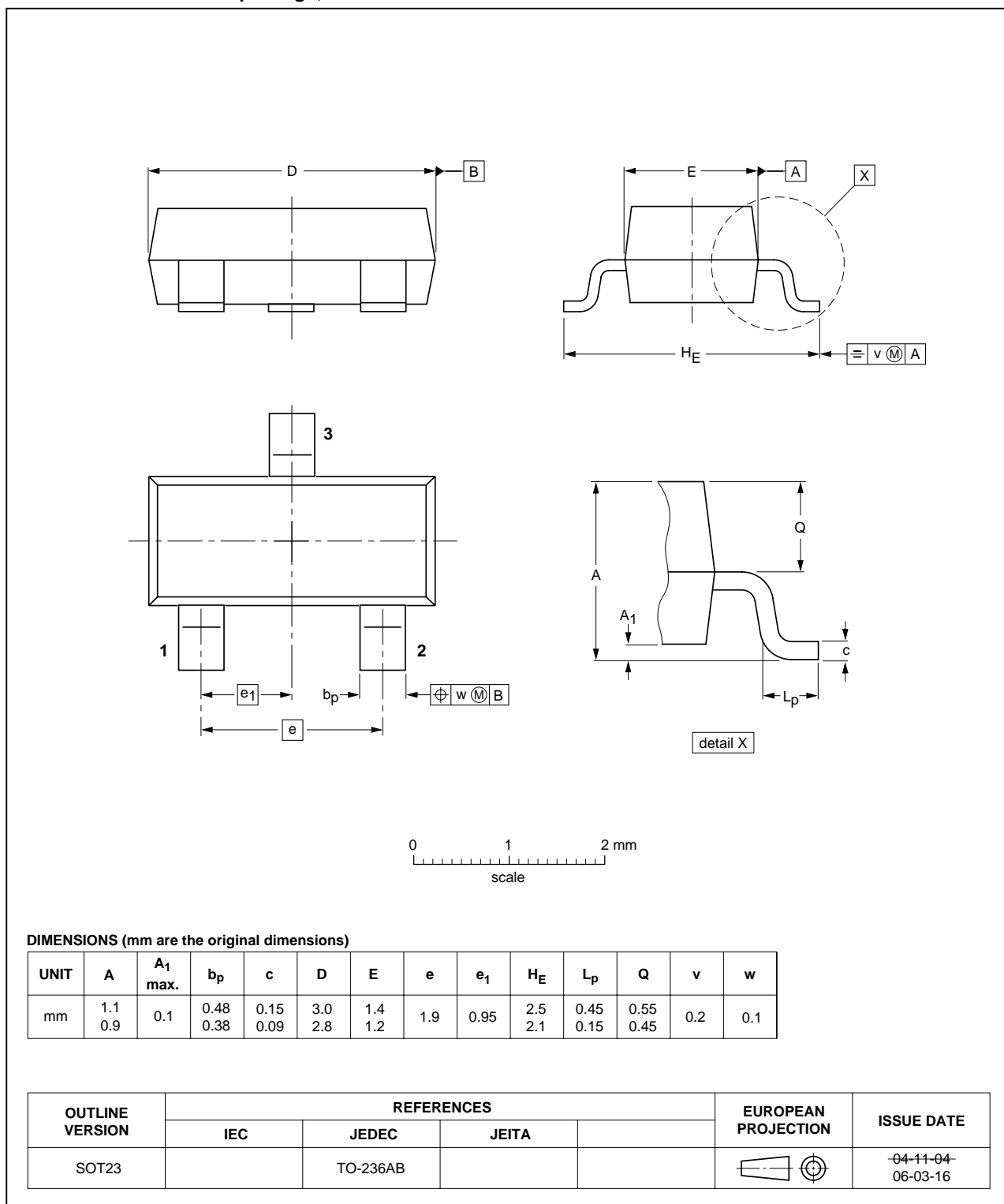
NPN general purpose transistors

PMBT6428; PMBT6429

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN general purpose transistors

PMBT6428; PMBT6429

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Jan 22

Document order number: 9397 750 12505

